

### High power NPN epitaxial planar bipolar transistor

#### **Features**

- High breakdown voltage V<sub>CEO</sub> = 120 V
- Complementary to 2STA1694
- Fast-switching speed
- Typical f<sub>t</sub> = 20 MHz
- Fully characterized at 125 °C

#### **Applications**

■ Audio power amplifier

### **Description**

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

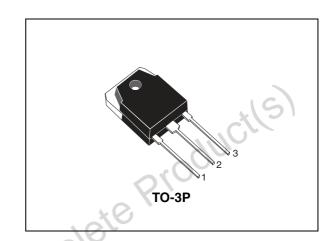


Figure 1. Internal schematic diagram

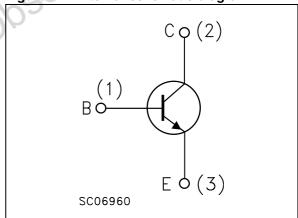


Table 1. Device summary

Order code	Marking	Package	Packaging
2STC4467	2STC4467	TO-3P	Tube

Electrical ratings 2STC4467

# 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	120	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	120	V
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ )	6	V
I <sub>C</sub>	Collector current	8	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	16	Α
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25 °C	80	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	*6	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case	max	1.563	°C/W
Opso	oduci(s) O	osonia.	1.303	G/W
Op				

2STC4467 **Electrical characteristics** 

#### **Electrical characteristics** 2

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$ 

Table 4. **Electrical characteristics** 

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Uni
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 120 V			10	μΔ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 6 V			10	μΑ
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 50 mA	120		cil	<b>5</b> \
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 100 μA	120	29/		٧
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1 mA	6			٧
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	I <sub>C</sub> = 3 A I <sub>B</sub> = 300 mA			1.5	V
$h_{FE}$	DC current gain	$I_C = 3 A$ $V_{CE} = 4 V$	70		140	
f <sub>T</sub>	Transition frequency	$I_C = 0.5 \text{ A}$ $V_{CE} = 12 \text{ V}$		20		MH
1. Pulsed du	uration = 300 μs, duty cycle ≤ 1.5%					
1. Pulsed du	uration = 300 μs, duty cycle ≤ 1.5%	3)				

Electrical characteristics 2STC4467

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve

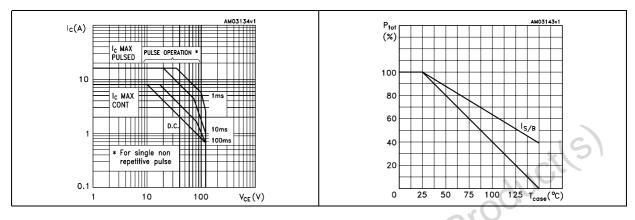


Figure 4. Output characteristics

Figure 5. DC current gain

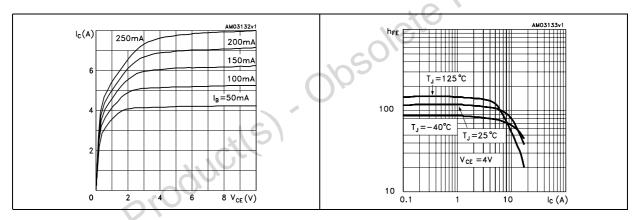
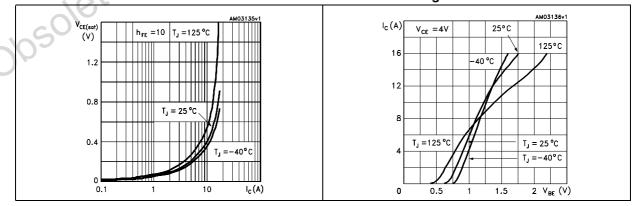


Figure 6. Collector-emitter saturation voltage Figure 7. Collector current vs base-emitter voltage



577

## 3 Package mechanical data

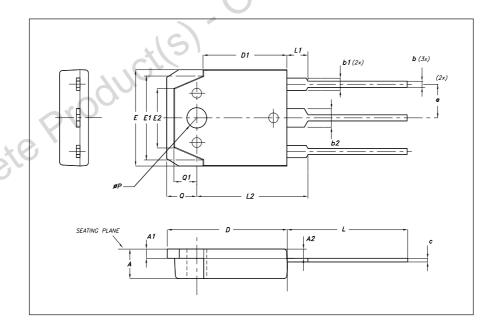
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and products status are available at: <a href="www.st.com">www.st.com</a>. ECOPACK® is an ST trademark.

Obsolete Product(s). Obsolete Product(s)

**577** 

#### **TO-3P Mechanical data**

DIM.		mm.			
DIWI.	MIN.	TYP	MAX.		
Α	4.6		5		
A1	1.45	1.50	1.65		
A2	1.20	1.40	1.60		
b	0.80	1	1.20		
b1	1.80		2.20		
b2	2.80		3.20		
С	0.55	0.60	0.75		
D	19.70	19.90	20.10		
D1		13.90			
E	15.40		15.80		
E1		13.60	100.		
E2		9.60			
е	5.15	5.45	5.75		
L	19.50	20	20.50		
L1		3.50	0		
L2	18.20	18.40	18.60		
Р	3.10		3.30		
Q		5			
Q1		3.80			



57

2STC4467 Revision history

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
22-Nov-2007	1	Initial release
30-Apr-2008	2	Document status promoted from preliminary data to datasheet.
11-Feb-2009	3	Added Section 2.1: Electrical characteristics (curves)

Obsolete Product(s). Obsolete Product(s)

#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2009 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

5//